

AMENDMENT TO ABSTRACT

DUAL ~~DAMASCENE~~ DAMASCENE PROCESS

ABSTRACT

A dual damascene process is disclosed. According to the dual damascene process of the present invention, a first recessed region through an intermetal dielectric layer is filled with a bottom protecting layer, and the bottom protecting layer and the intermetal dielectric layer are simultaneously etched to form a second recessed region that has a shallower depth and wider width than the first recessed region on the first recessed region by using an etch gas selectively etches the intermetal dielectric layer with respect to the bottom protecting layer. In other words, the etch selectivity ratio, the intermetal dielectric layer with respect to the bottom protecting layer, is preferably about 0.5 to about 1.5. Thus, it is possible to form a dual damascene structure without the formation of a byproduct or an oxide fence.